

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re REISSUE application of)
U.S. Patent No. 6,117,700)
Applicant: Kenji ORITA et al.) **Box Reissue**
Issued: September 12, 2000)
For: METHOD FOR FABRICATING)
SEMICONDUCTOR DEVICE)
HAVING GROUP III NITRIDE)

2/a

PRELIMINARY AMENDMENT
37 CFR 1.173(b), (c)

Commissioner for Patents
Washington, D.C. 20231

Sir:

Please preliminarily amend the above-identified application as follows:

In the Claims:

Please add new claims 16-43 as follows:

16. A method for fabricating a semiconductor device, comprising the steps of:
a) forming a semiconductor layer of a Group III nitride containing a dopant
over a substrate; and
b) applying RF power on the semiconductor layer, thereby making the
conductivity type of the semiconductor layer p-type.
17. The method of Claim 16, wherein the step b) is conducted in an ambient of
plasma.